

IRF7476PbF

HEXFET® Power MOSFET

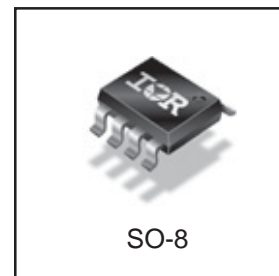
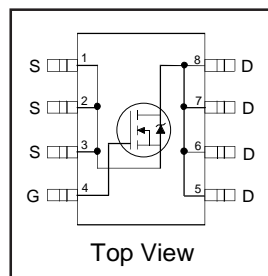
Applications

- High Frequency 3.3V and 5V input Point-of-Load Synchronous Buck Converters for Netcom and Computing Applications.
- Power Management for Netcom, Computing and Portable Applications.
- Lead-Free

Benefits

- Ultra-Low Gate Impedance
- Very Low $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$ max	I_D
12V	8.0mΩ@ $V_{GS} = 4.5V$	15A



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	12	V
V_{GS}	Gate-to-Source Voltage	±12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	15	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	12	
I_{DM}	Pulsed Drain Current ^①	120	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation ^④	2.5	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation ^④	1.6	W
	Linear Derating Factor	0.02	W/°C
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ^④	—	50	

Notes ^① through ^④ are on page 8
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Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	12	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.014	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	6.0	8.0	mΩ	V _{GS} = 4.5V, I _D = 15A ③
		—	12	30		V _{GS} = 2.8V, I _D = 12A ③
V _{GS(th)}	Gate Threshold Voltage	0.6	—	1.9	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	100	μA	V _{DS} = 9.6V, V _{GS} = 0V
		—	—	250		V _{DS} = 9.6V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V _{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V _{GS} = -12V

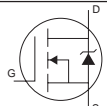
Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	31	—	—	S	V _{DS} = 6.0V, I _D = 12A
Q _g	Total Gate Charge	—	26	40	nC	I _D = 12A
Q _{gs}	Gate-to-Source Charge	—	4.6	—		V _{DS} = 10V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	11	—		V _{GS} = 4.5V
Q _{oss}	Output Gate Charge	—	17	—		V _{GS} = 0V, V _{DS} = 5.0V
t _{d(on)}	Turn-On Delay Time	—	11	—	ns	V _{DD} = 6.0V
t _r	Rise Time	—	29	—		I _D = 12A
t _{d(off)}	Turn-Off Delay Time	—	19	—		R _G = 1.8Ω
t _f	Fall Time	—	8.3	—		V _{GS} = 4.5V ③
C _{iss}	Input Capacitance	—	2550	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	2190	—		V _{DS} = 6.0V
C _{rss}	Reverse Transfer Capacitance	—	450	—		f = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	160	mJ
I _{AR}	Avalanche Current①	—	12	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	120		
V _{SD}	Diode Forward Voltage	—	0.87	1.2	V	T _J = 25°C, I _S = 12A, V _{GS} = 0V ③
		—	0.73	—		T _J = 125°C, I _S = 12A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	55	82	ns	T _J = 25°C, I _F = 12A, V _R = 12V
Q _{rr}	Reverse Recovery Charge	—	59	89		di/dt = 100A/μs ③
t _{rr}	Reverse Recovery Time	—	54	81	ns	T _J = 125°C, I _F = 12A, V _R = 12V
Q _{rr}	Reverse Recovery Charge	—	60	90		di/dt = 100A/μs ③

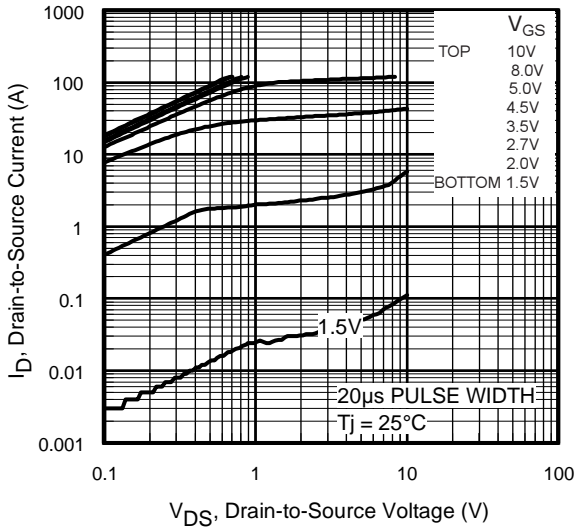


Fig 1. Typical Output Characteristics

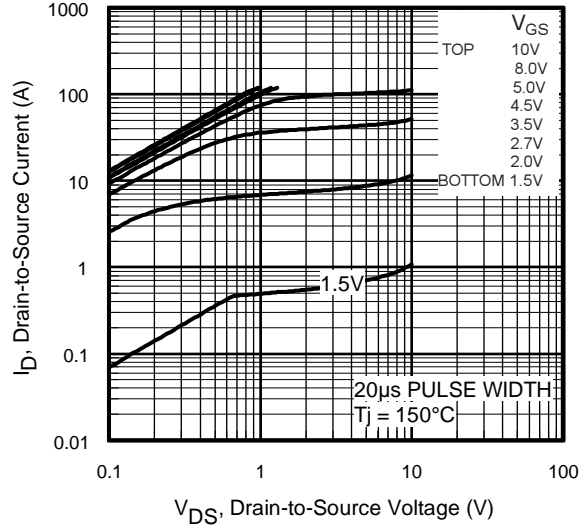


Fig 2. Typical Output Characteristics

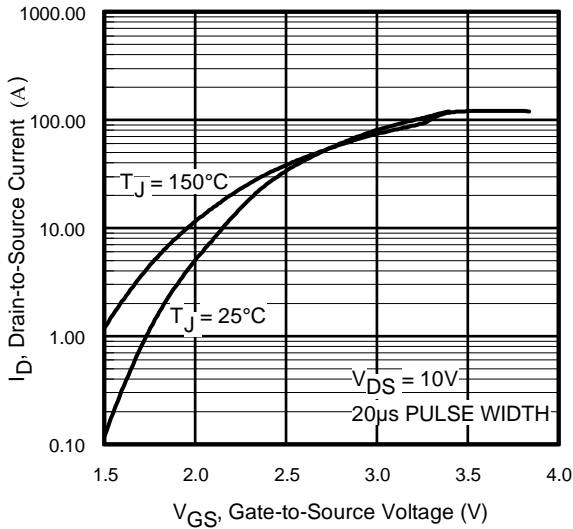


Fig 3. Typical Transfer Characteristics

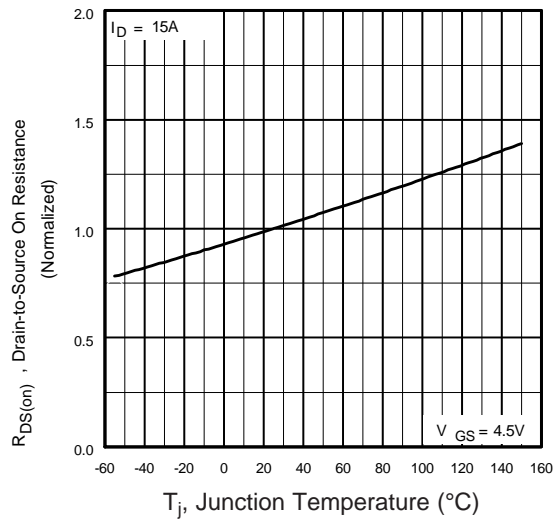


Fig 4. Normalized On-Resistance Vs. Temperature

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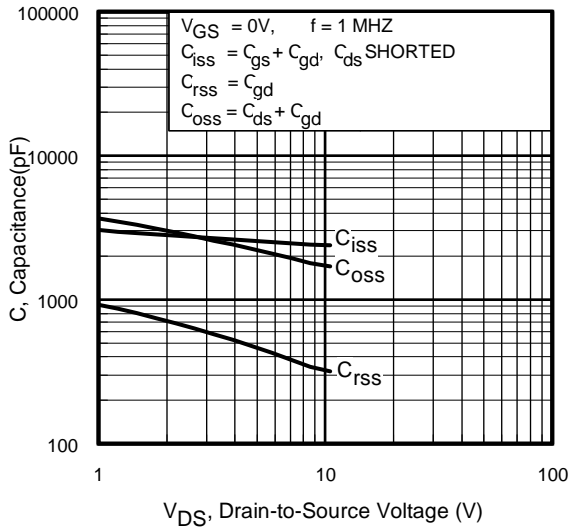


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

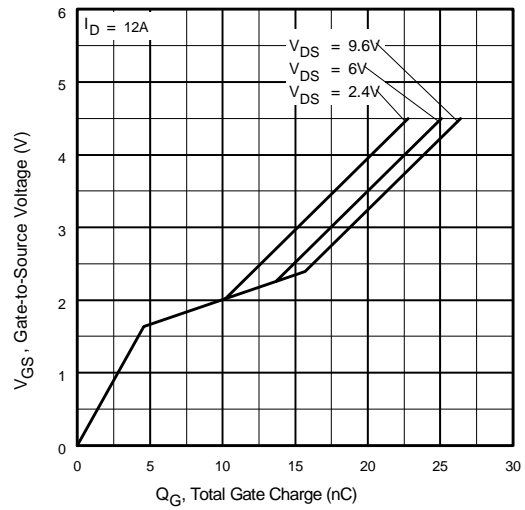


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

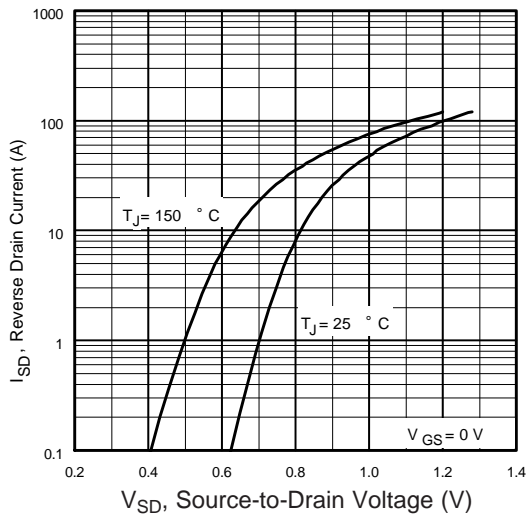


Fig 7. Typical Source-Drain Diode Forward Voltage

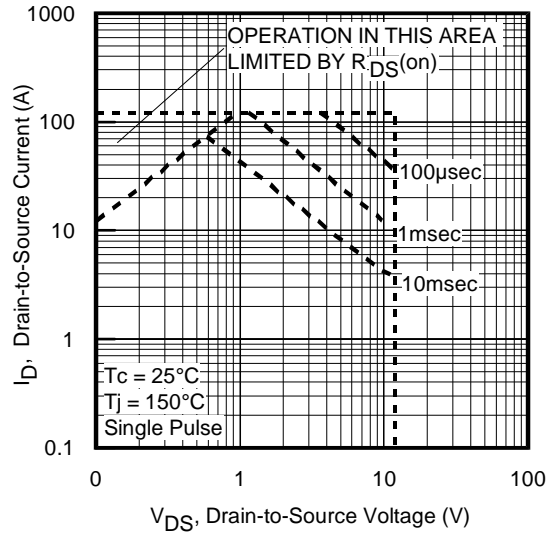


Fig 8. Maximum Safe Operating Area

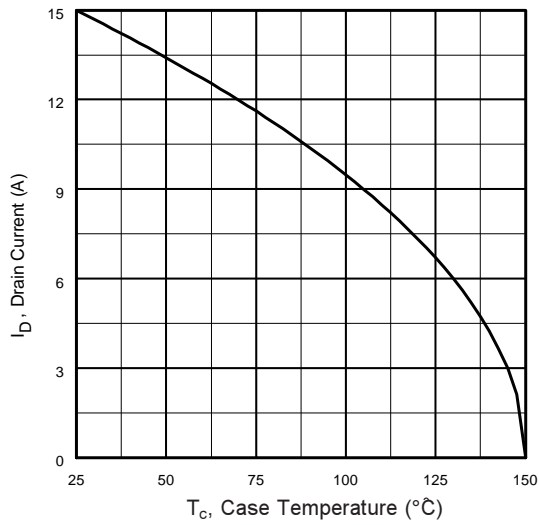


Fig 9. Maximum Drain Current Vs. Case Temperature

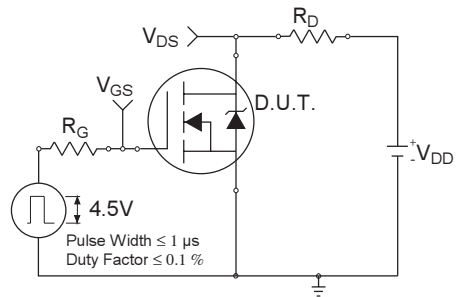


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

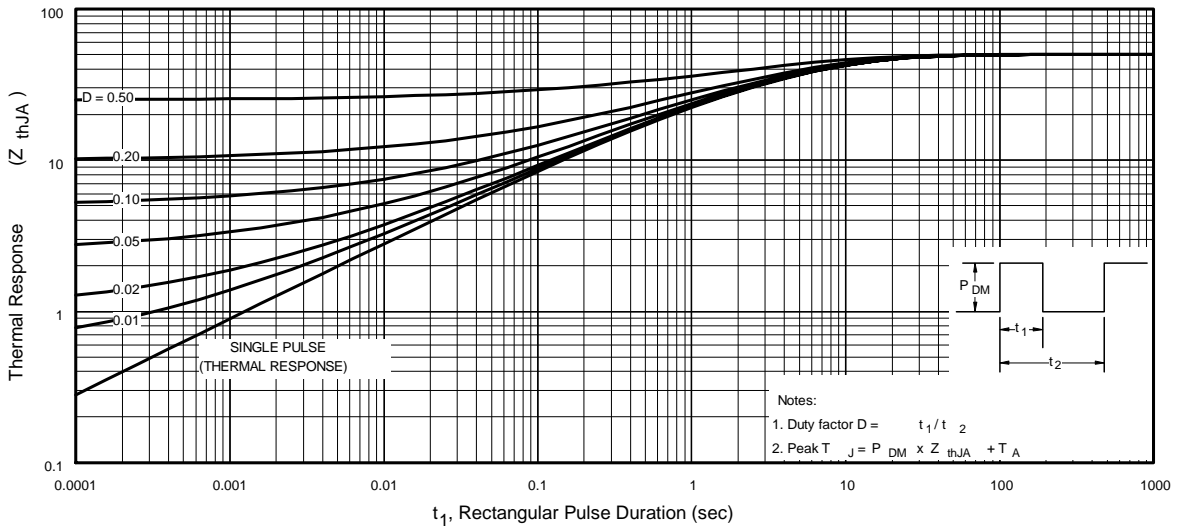


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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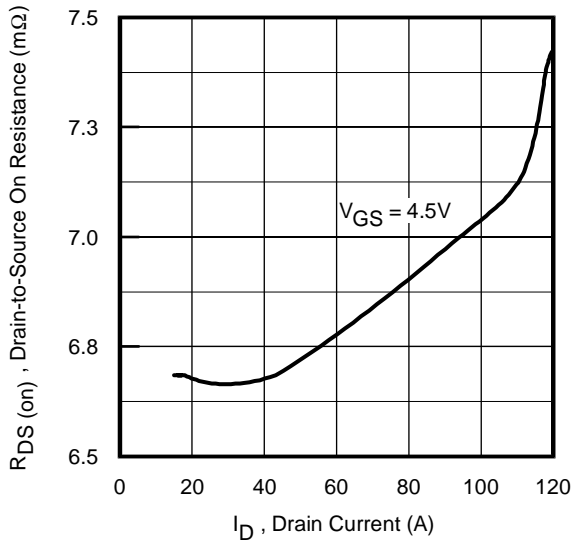


Fig 12. On-Resistance Vs. Drain Current

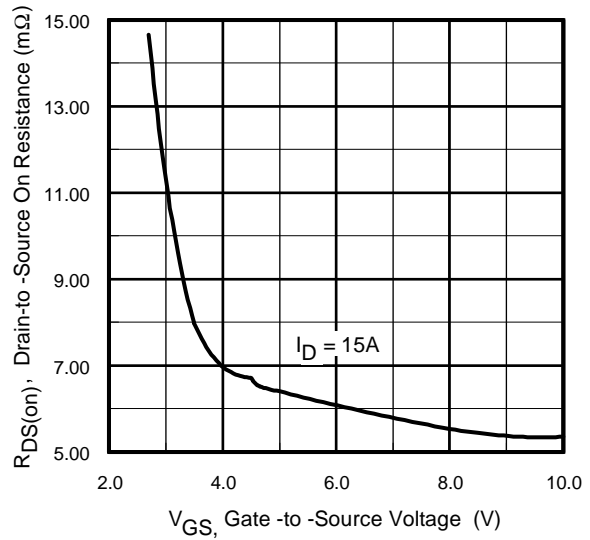


Fig 13. On-Resistance Vs. Gate Voltage

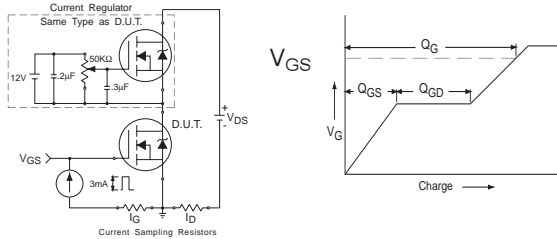


Fig 13a&b. Basic Gate Charge Test Circuit and Waveform



Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

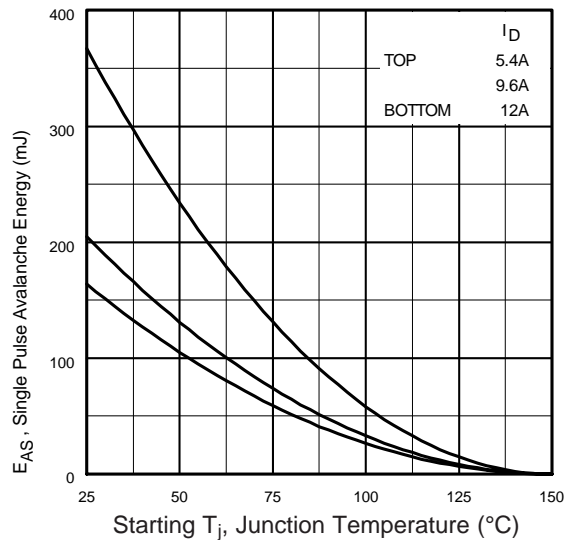
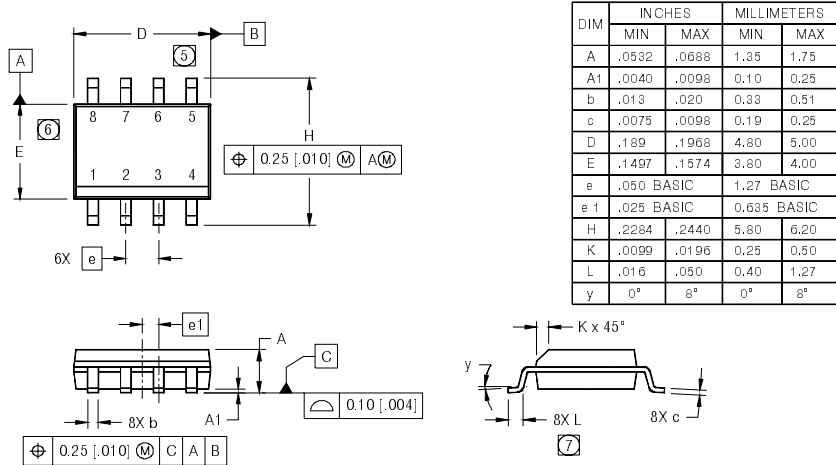


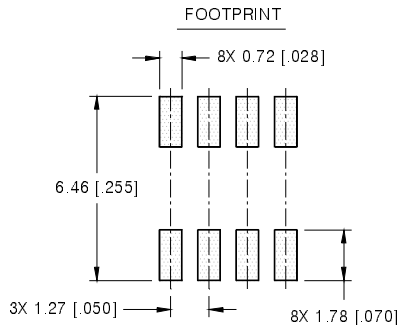
Fig 14c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Outline

Dimensions are shown in millimeters (inches)

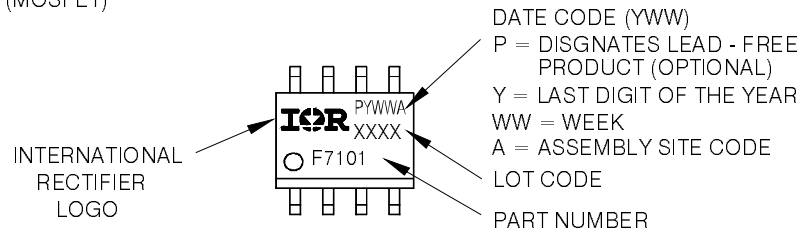


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
 5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
 6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
 7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

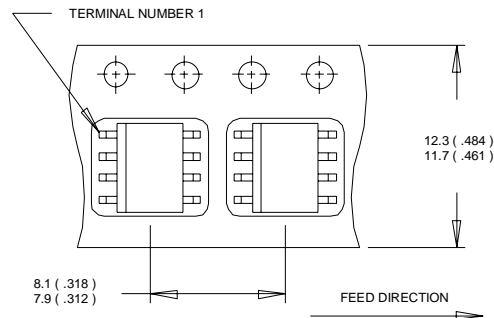


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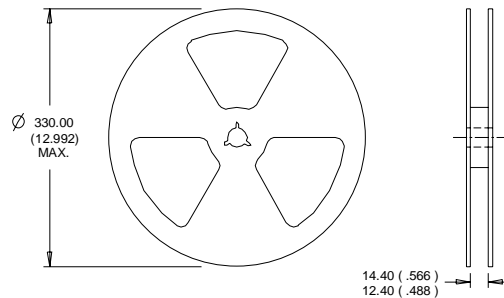
SO-8 Tape and Reel

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Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 2.3\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 12\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

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单击下面可查看定价，库存，交付和生命周期等信息

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